

General Description:

Using owner proprietary trench design and advanced Field Stop (FS) technology, offering superior conduction and Switching performances. RoHS Compliant.

V_{CES}	1200	V
I_C	100	A
$P_{tot} (T_C=25^{\circ}C)$	750	W
$V_{CE(sat)}$	1.65	V

Features:

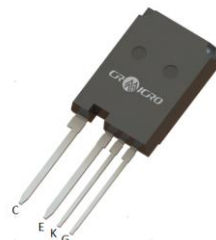
- FS Trench Technology, Positive temperature coefficient
- Low saturation voltage:

$V_{CE(sat)}$, TYP=1.65V @ $I_C=100A$, $V_{GE}=15V$;

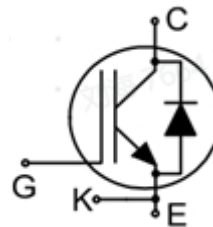
Applications

- Solar Inverter
- ESS
- UPS

Outline : TO-247PLUS-4A



Inner Circuit:



Package Parameters

Type	Marking	Package	Packing
CRG100T120BXA5HDZ	G100T120BXA5HDZ	TO-247PLUS-4A	Tube

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Rating	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate- Emitter Voltage	± 20	V
V_{GES}	Gate- Emitter Voltage ($t_p \leq 10\mu\text{s}, D < 0.01$)	± 30	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	180	A
	Collector Current @ $T_C = 100^\circ\text{C}$	100	
I_{CM}^{a1}	Pulsed Collector Current	400	A
I_F	Diode Continuous Forward Current @ $T_C = 25^\circ\text{C}$	200	A
	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	100	
I_{FM}	Diode Maximum Forward Current	400	A
P_D	Power Dissipation @ $T_C = 25^\circ\text{C}$	750	W
	Power Dissipation @ $T_C = 100^\circ\text{C}$	375	
T_{vjop}^{a2}	Operating Junction temperature range	$-40 \sim 175$	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	$-55 \sim 150$	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	270	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta_{JC}}$	Thermal Resistance, Junction to case for IGBT	--	0.20	$^\circ\text{C}/\text{W}$
$R_{\theta_{JC}}$	Thermal Resistance, Junction to case for Diode	--	0.56	$^\circ\text{C}/\text{W}$
$R_{\theta_{JA}}$	Thermal Resistance, Junction to Ambient	--	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics of the IGBT ($T_C = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
OFF Characteristics						
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V,I _{CE} =250uA	1200	--	--	V
I _{CES}	Collector Cut-off Current	V _{GE} =0V,V _{CE} =1200V	--	--	1	mA
I _{GES(F)}	Gate-Emitter Forward Leakage Current	V _{GE} =+20V	--	--	+250	nA
I _{GES(R)}	Gate-Emitter Reverse Leakage Current	V _{GE} =-20V	--	--	-250	nA
ON Characteristics						
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =100A ,V _{GE} =15V @ T _C = 25 ℃	--	1.65	2.4	V
		I _C =100A ,V _{GE} =15V @ T _C =175 ℃	--	2.1	--	V
V _{GE(th)}	Gate - Emitter Threshold Voltage	I _C =1.6mA ,V _{CE} =V _{GE}	4.0	5.4	7.5	V
Pulse width tp≤300μs,δ≤2%						

Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} =30V,V _{GE} =0V f=1MHz	--	14712	--	pF
C _{oes}	Output Capacitance		--	225	--	
C _{res}	Reverse Transfer Capacitance		--	59	--	
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{CE} =600V,I _C =100A, R _g =10Ω,V _{GE} =15V, Inductive Load, T _J =25℃ ,	--	72	--	ns
t _r	Rise Time		--	29	--	
t _{d(off)}	Turn-Off Delay Time		--	758	--	
t _f	Fall Time		--	27	--	
E _{on}	Turn-On Switching Loss	V _{CE} =600V,I _C =100A, R _g =10Ω,V _{GE} =15V, Inductive Load, T _J =25℃ ,	--	2.5	--	mJ
E _{off}	Turn-Off Switching Loss		--	3.2	--	
E _{ts}	Total Switching Loss		--	5.7	--	
t _{d(on)}	Turn-on Delay Time	V _{CE} =600V,I _C =100A, R _g =10Ω,V _{GE} =15V, Inductive Load, T _J =175℃	--	56	--	ns
t _r	Rise Time		--	32	--	
t _{d(off)}	Turn-Off Delay Time		--	893	--	
t _f	Fall Time		--	87	--	
E _{on}	Turn-On Switching Loss	V _{CE} =600V,I _C =100A, R _g =10Ω,V _{GE} =15V, Inductive Load, T _J =175℃	--	3.7	--	mJ
E _{off}	Turn-Off Switching Loss		--	5.2	--	
E _{ts}	Total Switching Loss		--	8.9	--	
Q _g	Total Gate Charge	V _{CE} =960V,I _C =100A, V _{GE} =15V,	--	672	--	nC
Q _{ge}	Gate to Emitter Charge		--	94	--	
Q _{gc}	Gate to Collector Charge		--	272	--	
Electrical Characteristics of the DIODE						
V _F	Diode Forward Voltage	I _F =100A TC=25℃	--	2.7	3.2	V
		I _F =100A TC=175℃	--	2.3	--	V
t _{rr}	Reverse Recovery Time	I _F =100A di/dt=100A/μs	--	122	--	ns
I _{rrm}	Reverse Recovery Current		--	5.2	--	A
Q _{rr}	Reverse Recovery Charge		--	317	--	nC

Notes:

a1: Repetitive rating; pulse width limited by maximum junction temperature ;

a2: Overload condition, it is allowed to operate under the maximum junction temperature $T_{vjop} = 175^\circ C$, the maximum duty cycle is less than 20% (lasting for 60s at most);

Typical Performance Characteristics

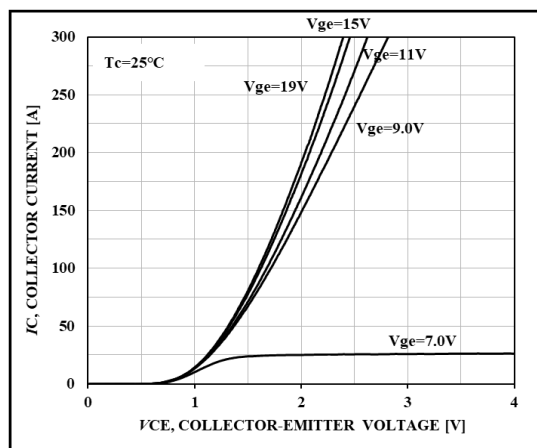


Figure 1. Output Characteristics

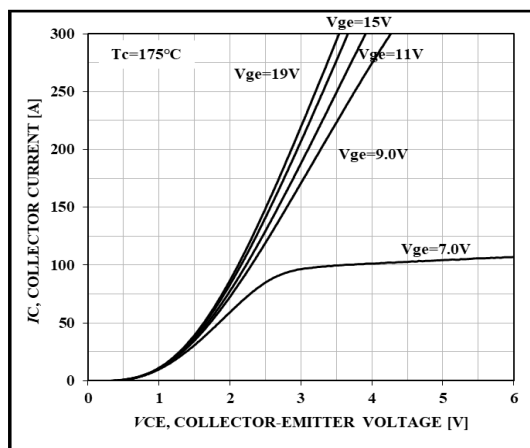


Figure 2. Output Characteristics

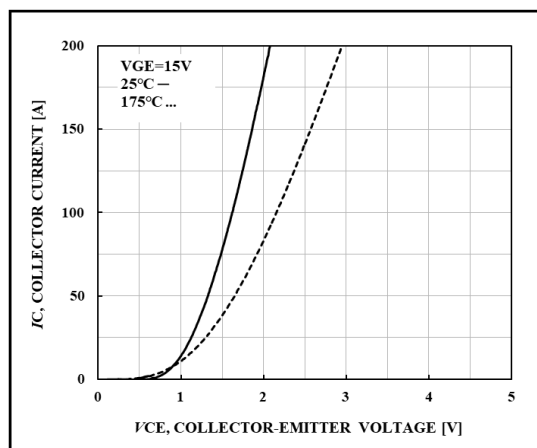


Figure 3. Saturation Voltage Characteristics

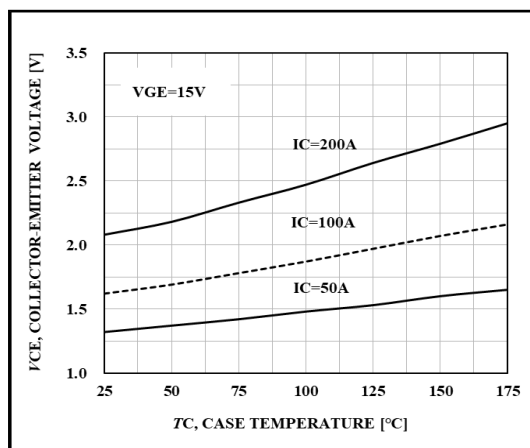


Figure 4. Saturation Voltage - T_C Characteristics

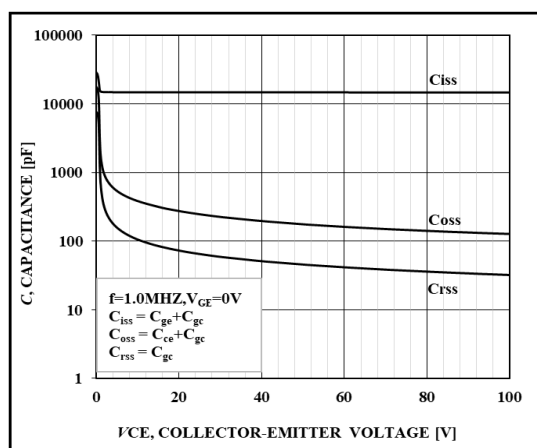


Figure 5. Capacitance Characteristics

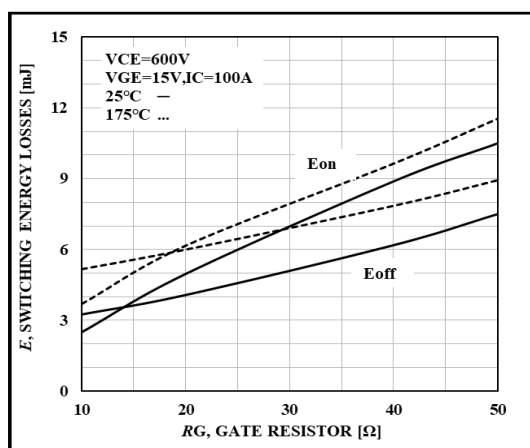


Figure 6. Switching Loss- R_G Characteristics

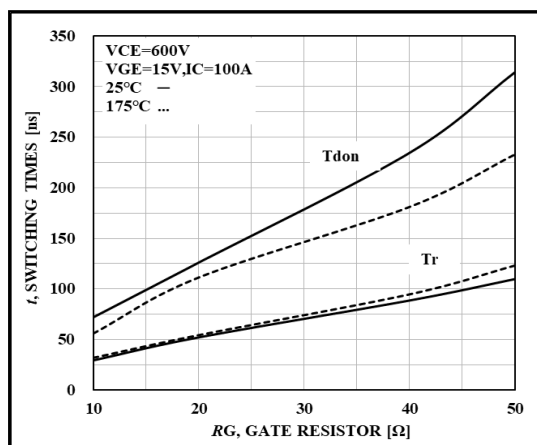


Figure 7. Switching Time-R_G Characteristics

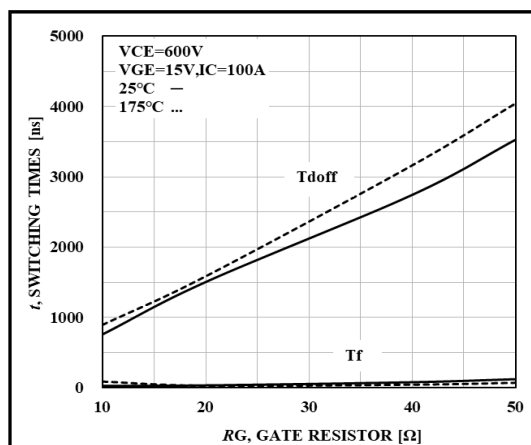


Figure 8. Switching Time-R_G Characteristics

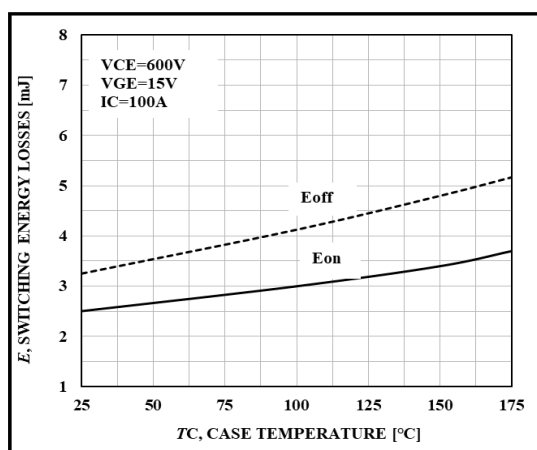


Figure 9. Switching Loss-T_C Characteristics

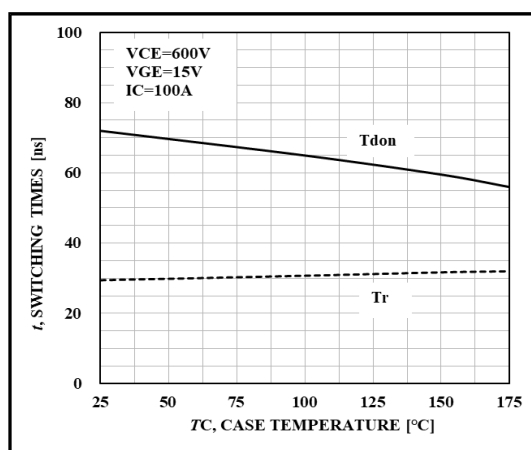


Figure 10. Switching Time-T_C Characteristics

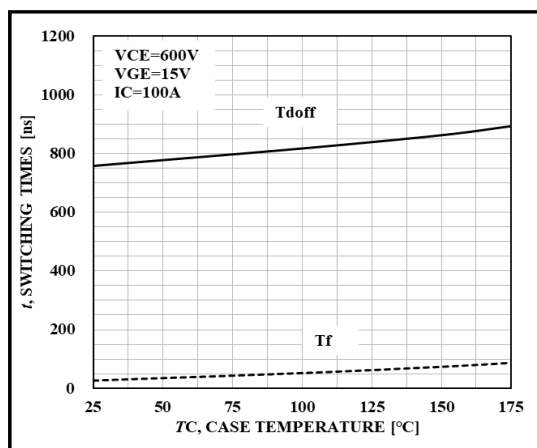


Figure 11. Switching Time-T_C Characteristics

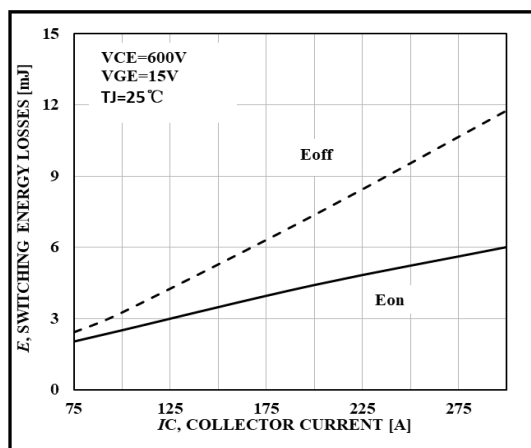


Figure 12. Switching Loss-I_C Characteristics

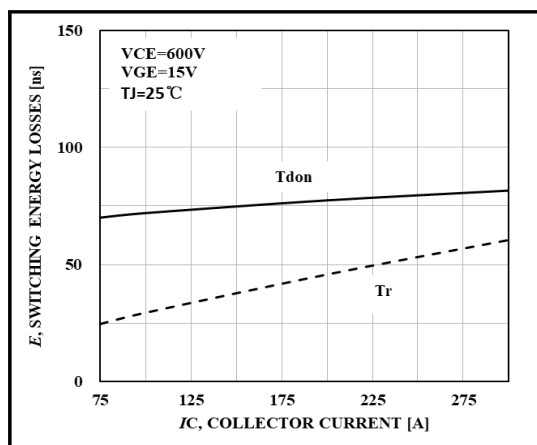


Figure 13. Switching Time-IC Characteristics

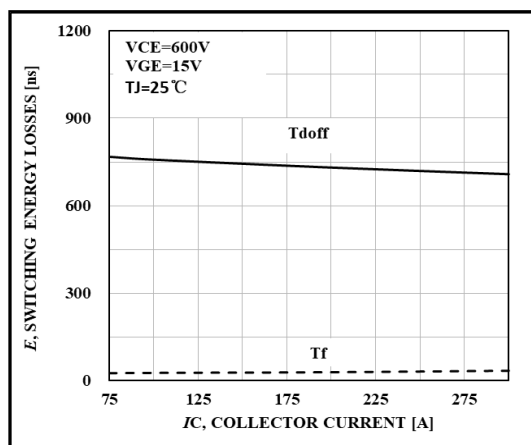


Figure 14. Switching Time-IC Characteristics

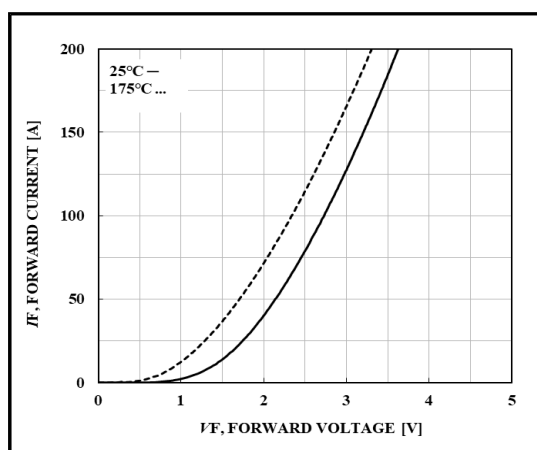


Figure 15. Diode Forward Characteristics

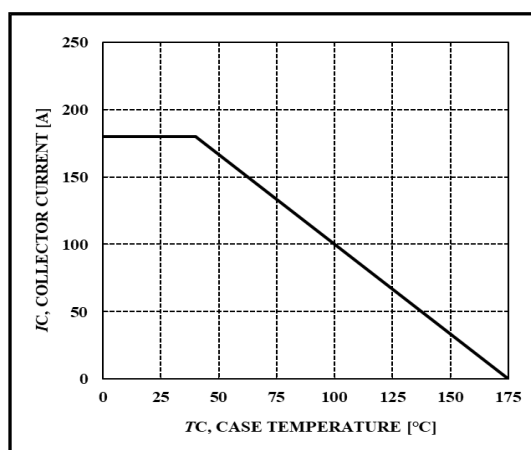


Figure 16. Collector Current-Tc Characteristics
(Tj ≤ 175°C)

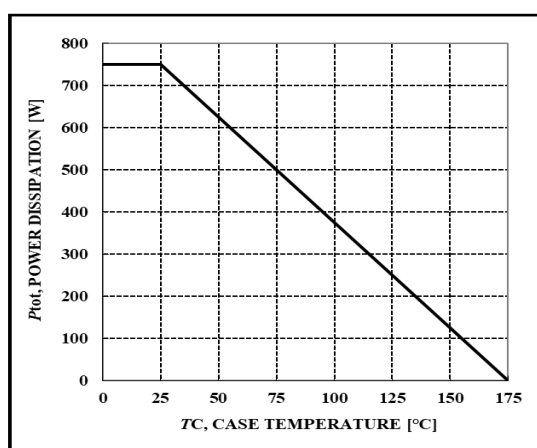


Figure 17. Power Dissipation-Tc Characteristics
(Tj ≤ 175°C)

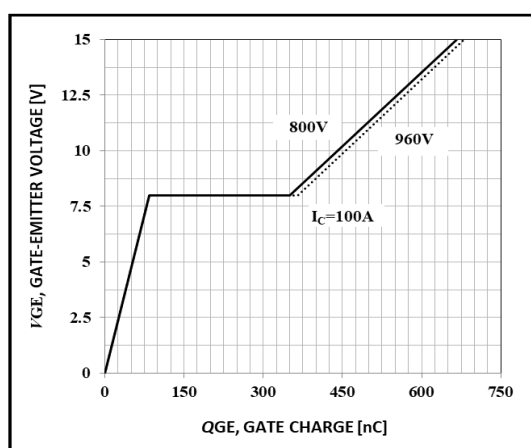


Figure 18. Gate Charge Characteristics

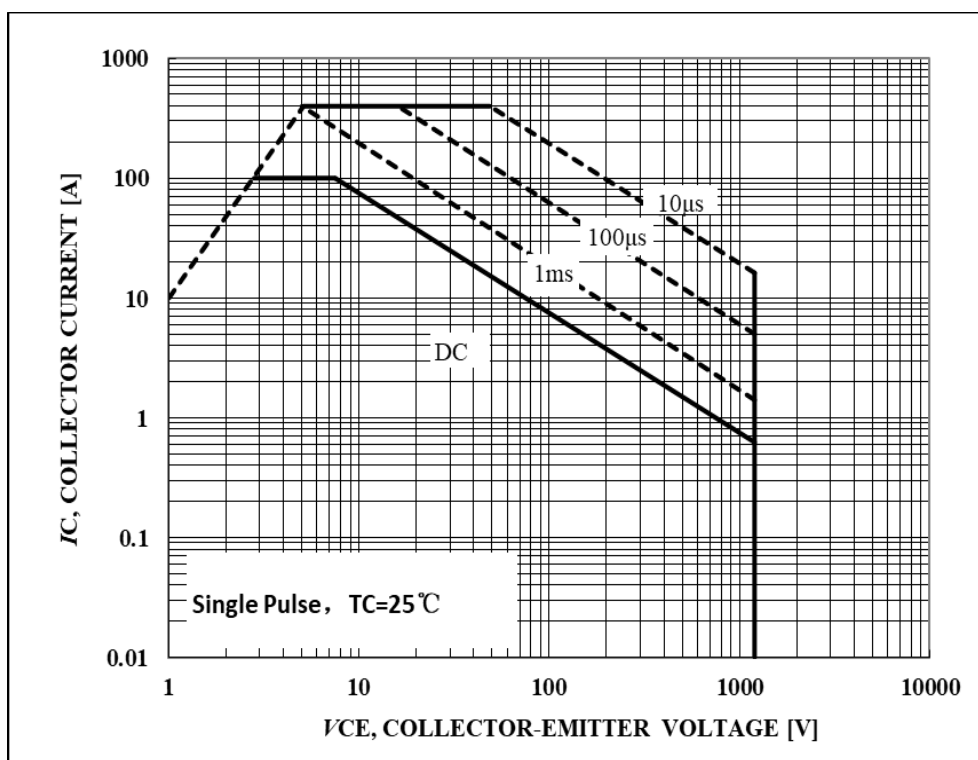


Figure 19. Forward Bias Safe Operating Area

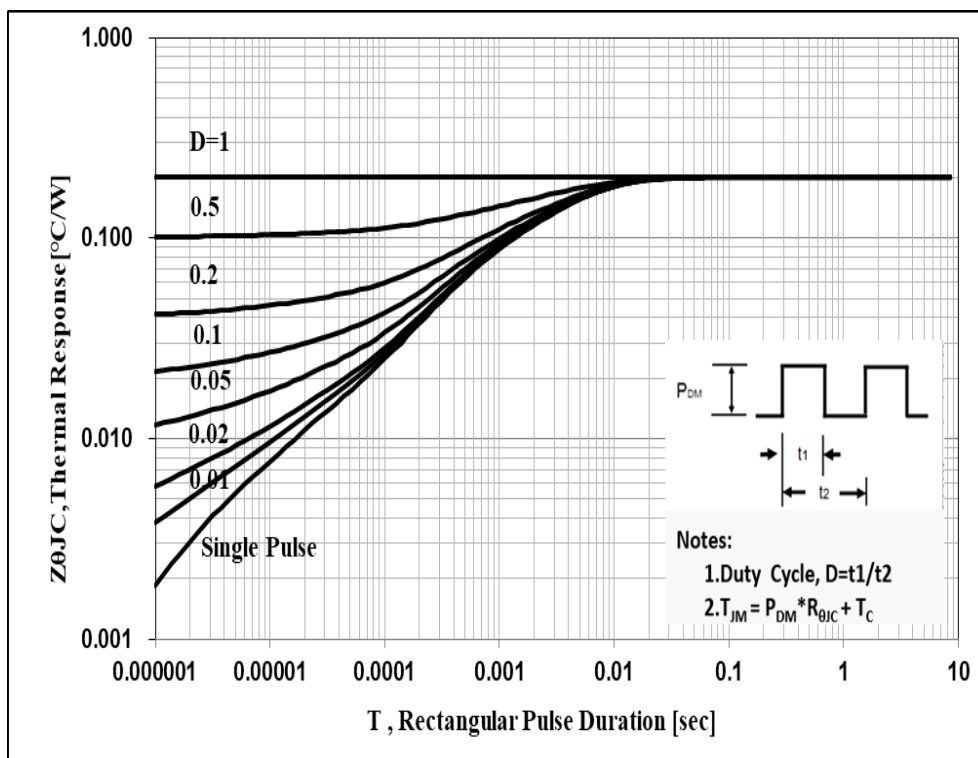
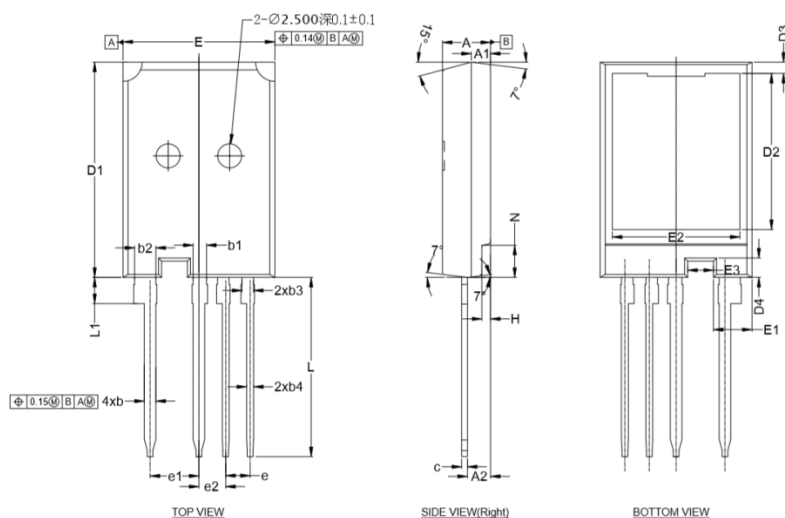


Figure 20. IGBT Transient Thermal Impedance

Package Information



项 目	规范(mm)	
	MIN	MAX
A	4.85	5.15
A1	1.90	2.20
A2	2.15	2.65
b	1.07	1.33
b1	1.30	1.55
b2	2.10	2.35
b3	1.10	1.45
b4	0.60	0.84
c	0.50	0.70
D1	22.20	22.60
D2	15.90	16.60
D3	0.97	1.37
D4	1.90	2.10
E	15.50	16.10
E1	3.85	4.15
E2	13.05	13.55
E3	2.53	2.83
e	2.54 BSC	
e1	5.08 BSC	
e2	2.79 BSC	
L	18.40	18.90
L1	2.50	2.90
H	0.80	1.00
N	3.24	3.44

TO-247PLUS-4A Package

The name and content of poisonous and harmful material in products

Part's Name Limit	Hazardous Substance									
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE	DIBP	DEHP	DBP	BBP
	≤0.1%	≤0.1%	≤0.01%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%
Lead Frame	○	○	○	○	○	○	○	○	○	○
Molding	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○	○	○	○	○
Solder	×	○	○	○	○	○	○	○	○	○
Note	○: Means the hazardous material is under the criterion of 2011/65/EU. ×: Means the hazardous material exceeds the criterion of 2011/65/EU. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.									

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. IGBTs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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Revision History		
Revision	Date	Major changes
1.0	2025/5/14	Initial release